

40V NPN MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

Features

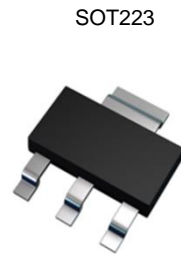
- $BV_{CEO} > 40V$
- $I_C = 5A$ High Continuous Collector Current
- $I_{CM} = 20A$ Peak Pulse Current
- Low Saturation Voltage $V_{CE(sat)} < 120mV @ 1A$
- $R_{SAT} = 50m\Omega @ 5A$ for a Low Equivalent On-Resistance
- h_{FE} Specified up to 10A for a High Gain Hold-Up
- Complementary PNP Type: FZT1151A
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

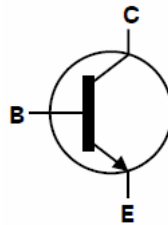
- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 $\text{\textcircled{3}}$
- Weight: 0.112 grams (Approximate)

Applications

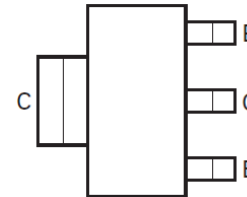
- Solenoid, Relay and Actuator Drivers
- DC Modules
- Motor Control



Top View



Device Symbol



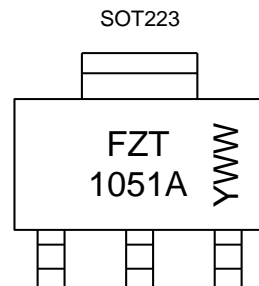
Top View
Pin-Out

Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT1051ATA	AEC-Q101	FZT1051A	7	12	1,000
FZT1051ATC	AEC-Q101	FZT1051A	13	12	4,000

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



FZT 1051A = Product Type Marking Code
 YYWW = Date Code Marking
 Y or \bar{Y} = Last Digit of Year (ex: 5= 2015)
 WW or \bar{WW} = Week Code (01~53)

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	150	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	5	A
Peak Pulse Current	I _{CM}	10	A
Base Current	I _B	1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

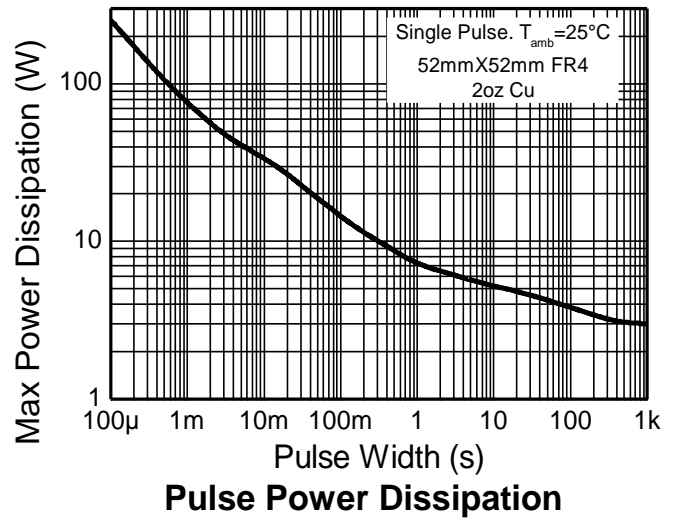
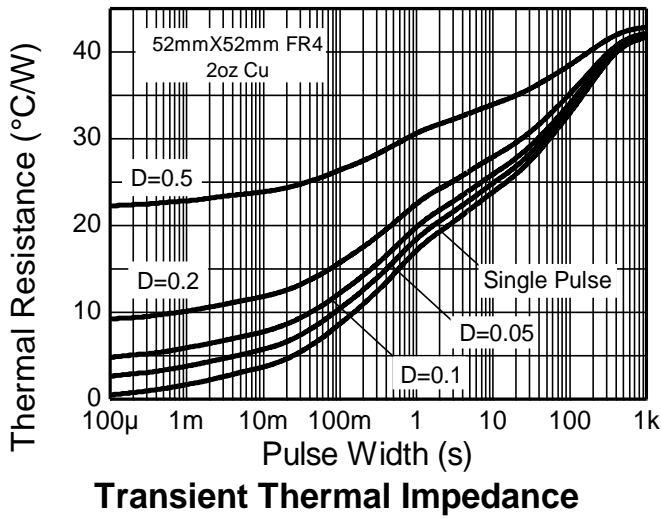
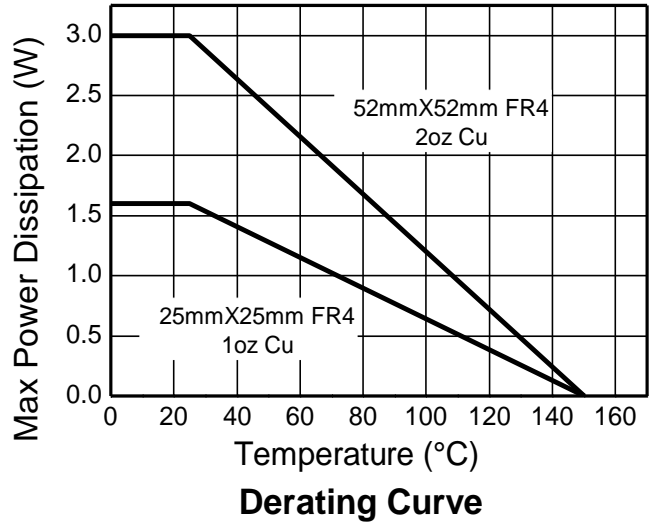
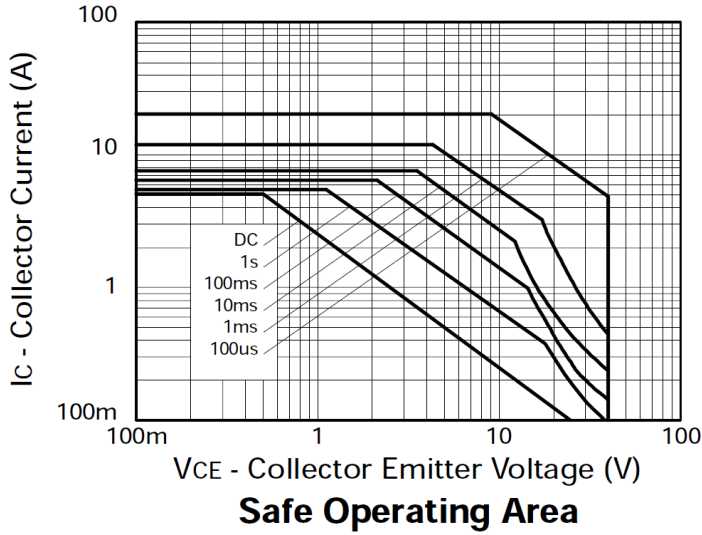
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	(Note 5)	3.0
		(Note 6)	2.0
		(Note 7)	1.6
		(Note 8)	1.2
Thermal Resistance, Junction to Ambient	R _{θJA}	(Note 5)	41.7
		(Note 6)	62.5
		(Note 7)	78.1
		(Note 8)	104
Thermal Resistance Junction to Lead	R _{θJL}	10.9	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
 - Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
 - Same as Note 5, except the device is mounted on minimum recommended pad layout.
 - Thermal resistance from junction to solder-point (at the end of the collector lead).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

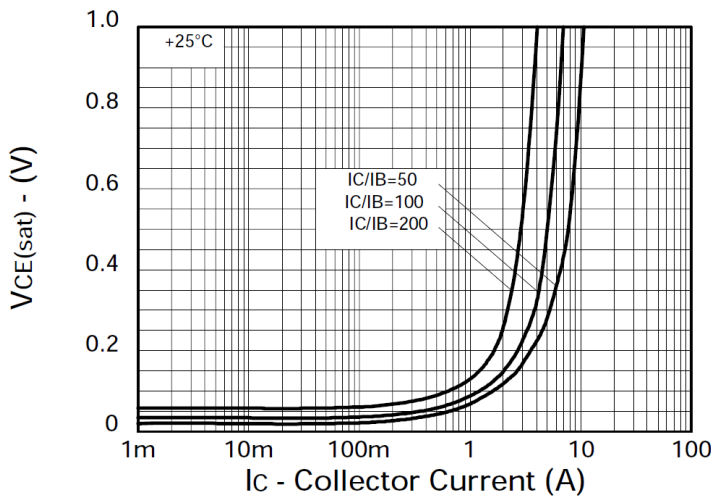


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

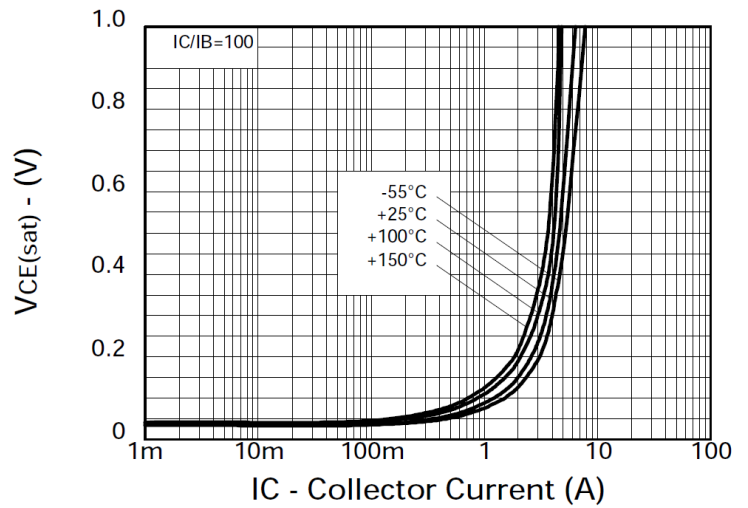
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	190	–	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	BV _{CES}	150	190	–	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	BV _{CEV}	150	190	–	V	I _C = 100μA, V _{EB} = 1V
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	40	60	–	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	–	V	I _E = 100μA
Collector Cut-Off Current	I _{CBO}	–	<1	10	nA	V _{CB} = 120V
Collector Cut-Off Current	I _{CES}	–	<1	10	nA	V _{CB} = 120V, T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	–	<1	10	nA	V _{EB} = 6V
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	–	17	25	mV	I _C = 200mA, I _B = 10mA
		–	85	120		I _C = 1A, I _B = 10mA
		–	140	180		I _C = 2A, I _B = 20mA
		–	250	340		I _C = 5A, I _B = 100mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	–	980	1100	mV	I _C = 5A, I _B = 100mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	–	915	1000	mV	I _C = 5A, V _{CE} = 2V
DC Current Gain (Note 11)	h _{FE}	290	440	–	–	I _C = 10mA, V _{CE} = 2V
		270	450	1200		I _C = 1A, V _{CE} = 2V
		130	220	–		I _C = 5A, V _{CE} = 2V
		40	55	–		I _C = 10A, V _{CE} = 2V
Output Capacitance	C _{obo}	–	27	40	pF	V _{CB} = 10V, f = 1MHz
Current Gain-Bandwidth Product	f _T	–	155	–	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz
Switching Times	t _{on}	–	220	–	ns	I _C = 3A, V _{CC} = 10V, I _{B1} = -I _{B2} = 30mA
	t _{off}	–	540	–		

Note: 11. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%

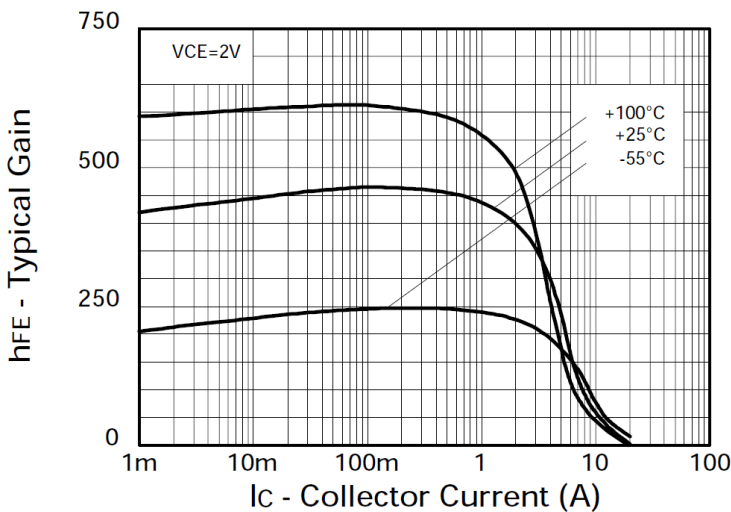
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



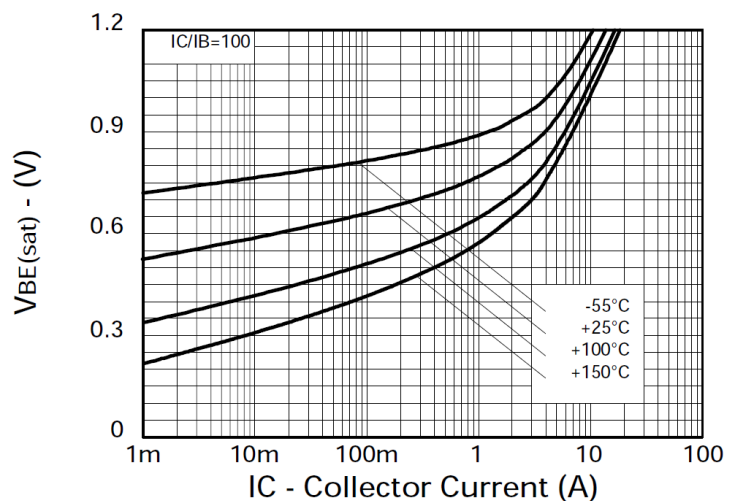
$V_{CE(sat)}$ v I_C



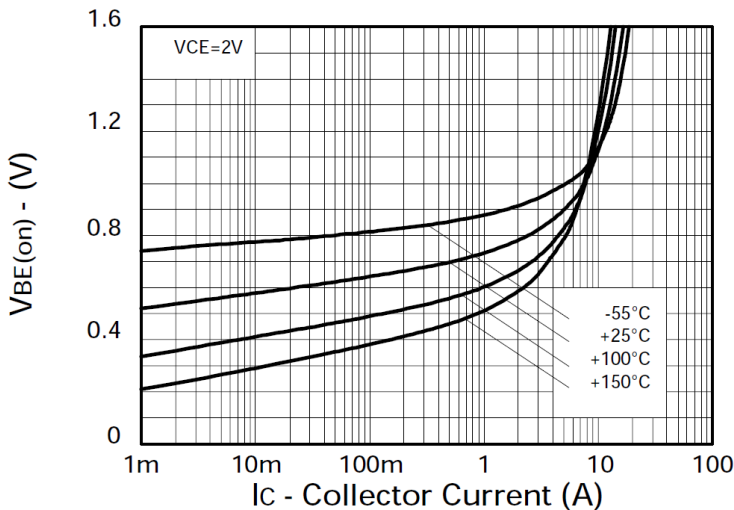
$V_{CE(sat)}$ v I_C



h_{FE} v I_C



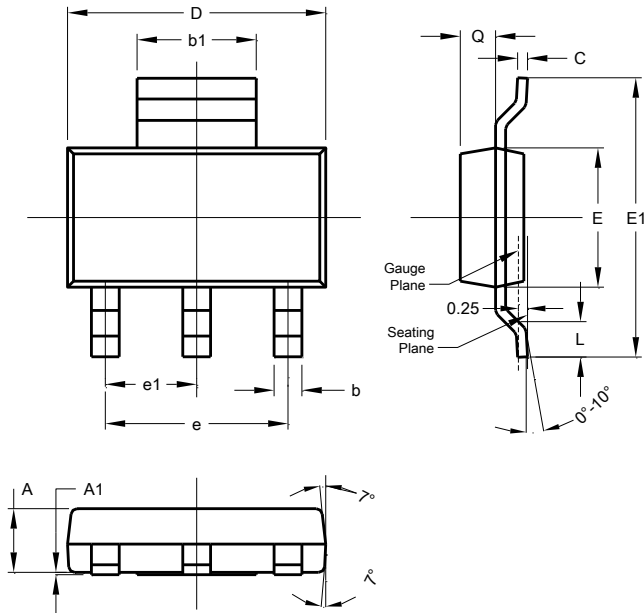
$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C

Package Outline Dimensions

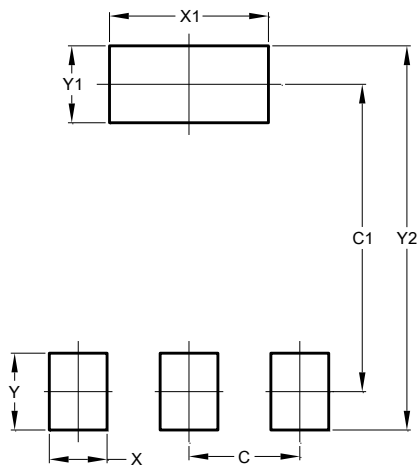
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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